**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020M-6 (SOT1220-4) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- · Low threshold voltage
- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.6 mm
- Exposed drain pad for excellent thermal conduction

## 3. Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- · Computing power management

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-12	V
$V_{GS}$	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	-16	Α
Static characte	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -11 \text{ A}; T_j = 25 \text{ °C}$		-	7.3	8.8	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



12 V, P-channel Trench MOSFET

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		
2	D	drain		D
3	G	gate		
4	S	source	2 5	G $($
5	D	drain	3 8 4	
6	D	drain	Transparent top view	S
7	D	drain	DFN2020M-6 (SOT1220-4)	017aaa094
8	S	source		

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PMPB06R7VP		plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 x 2 x 0.60 mm	SOT1220-4		

# 7. Marking

### Table 4. Marking codes

Type number	Marking code
PMPB06R7VP	RB

12 V, P-channel Trench MOSFET

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-12	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-16	А
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-11	А
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-7	A
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	-144	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	3.7	W
			[1]	-	1.7	W
		T <sub>sp</sub> = 25 °C		-	18	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain d	iode		'	'	·	•
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.5	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

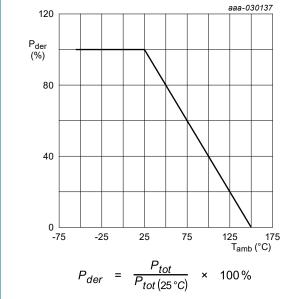


Fig. 1. Normalized total power dissipation as a function of ambient temperature

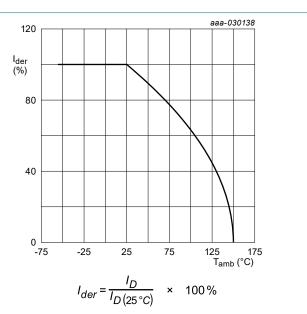


Fig. 2. Normalized continuous drain current as a function of ambient temperature

### 12 V, P-channel Trench MOSFET

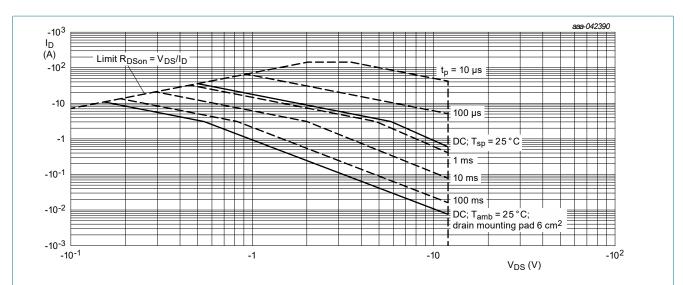


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

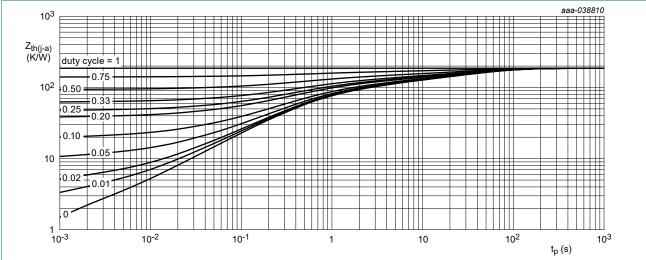
12 V, P-channel Trench MOSFET

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

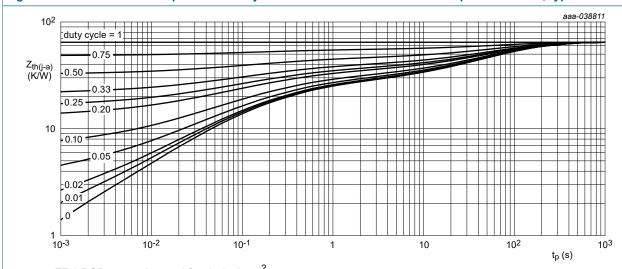
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-a)	thermal resistance from	in free air	[1]	-	187	216	K/W
	junction to ambient		[2]	-	65	75	K/W
		in free air; t ≤ 5 s	[2]	-	30	34	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	4	7	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

12 V, P-channel Trench MOSFET

# 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-12	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.4	-0.65	-0.9	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -12 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
		V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -11 A; T <sub>j</sub> = 25 °C	-	7.3	8.8	mΩ
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -11 A; T <sub>j</sub> = 150 °C	-	12	14	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -8.5 A; $T_j$ = 25 °C	-	10.5	14.6	mΩ
		V <sub>GS</sub> = -1.8 V; I <sub>D</sub> = -3 A; T <sub>j</sub> = 25 °C	-	19	32	mΩ
		V <sub>GS</sub> = -1.5 V; I <sub>D</sub> = -0.5 A; T <sub>j</sub> = 25 °C	-	30	75	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_D$ = -10.3 A; $T_j$ = 25 °C	-	27.3	-	S
$R_G$	gate resistance	f = 1 MHz	-	5.3	-	Ω
Dynamic ch	naracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -6 \text{ V}; I_D = -10.3 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	32	46	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	4.3	-	nC
Q <sub>GD</sub>	gate-drain charge	1	-	10.3	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -6 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	2700	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	700	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	650	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -6 \text{ V}; I_D = -10 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	24	-	ns
t <sub>d(off)</sub>	turn-off delay time	1 – –	-	86	-	ns
t <sub>f</sub>	fall time	1	-	69	-	ns
Source-drai	in diode		1		-	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -1.5 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.7	-1.2	V

#### 12 V, P-channel Trench MOSFET

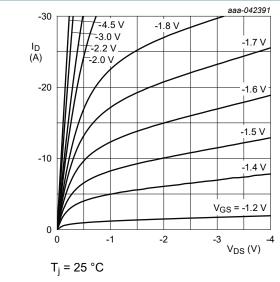


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

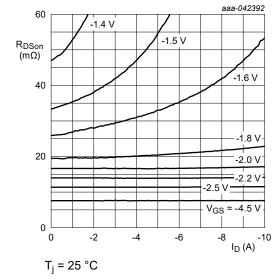


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

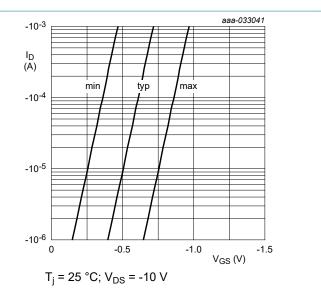


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

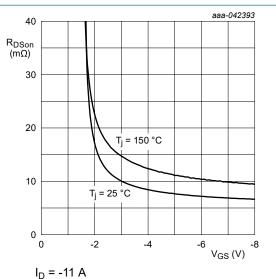


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 12 V, P-channel Trench MOSFET

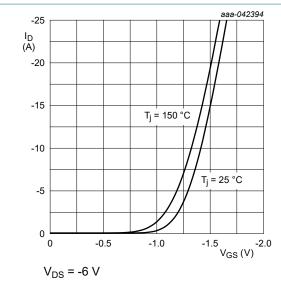


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

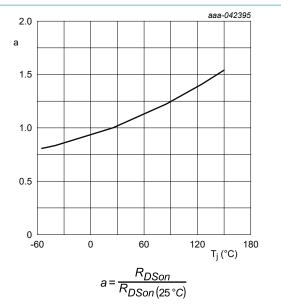


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

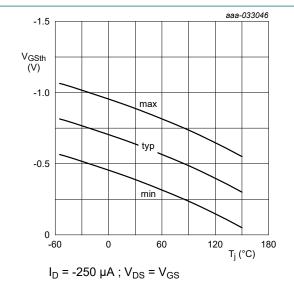
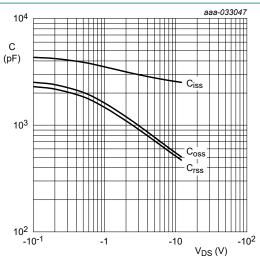


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

## 12 V, P-channel Trench MOSFET

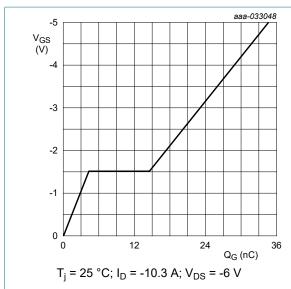


Fig. 14. Gate-source voltage as a function of gate charge; typical values

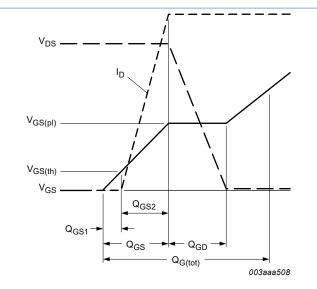


Fig. 15. Gate charge waveform definitions

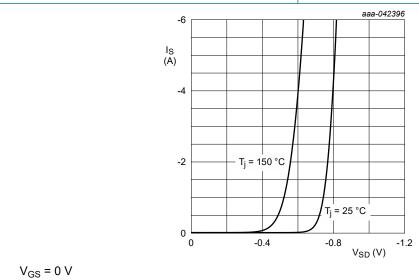
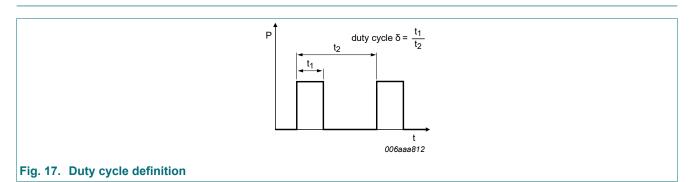


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information



12 V, P-channel Trench MOSFET

# 12. Package outline

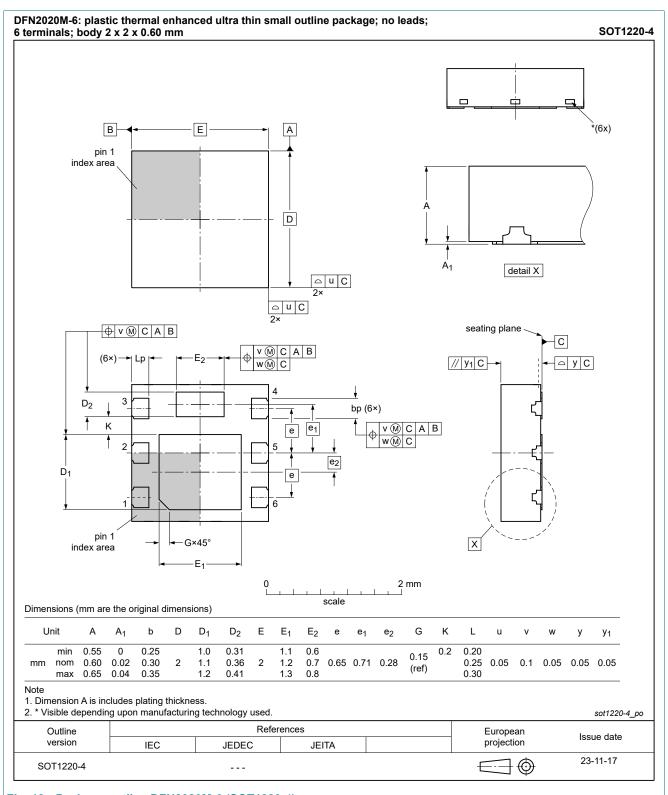
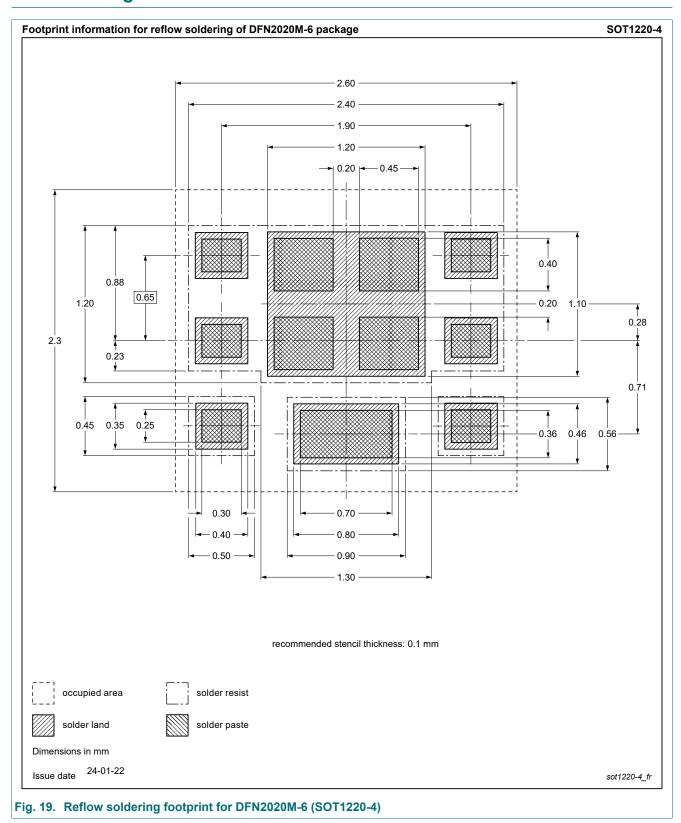


Fig. 18. Package outline DFN2020M-6 (SOT1220-4)

12 V, P-channel Trench MOSFET

# 13. Soldering



12 V, P-channel Trench MOSFET

# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB06R7VP v.1	20250221	Product data sheet	-	-

### 12 V, P-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### 12 V, P-channel Trench MOSFET

## **Contents**

General description	. 1
Features and benefits	1
Applications	1
Quick reference data	. 1
Pinning information	. 2
Ordering information	. 2
Marking	. 2
Limiting values	3
Thermal characteristics	5
Characteristics	. 6
Test information	. 9
Package outline1	10
Soldering 1	11
Revision history1	12
Legal information1	
	Features and benefits

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